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Points awarded:	Not ID:

Lab Module 913 Mic and Preamp

Procedure

Build the following circuit. Note that the dotted line shows the entire electret microphone capsule and that the MOSFET is embedded in that capsule (it is *not* a discrete element). The microphone has a negative side (polarity). See the datasheet. Use the rechargeable NiMH battery to supply V_{CC} . Also, note that there is a jumper wire connecting the wiper of the $10~k\Omega$ trimpot to the $680~\Omega$ resistor. There are portions of relevant datasheets on the back side of this paper.

Turn on the oscilloscope and press the Default Setup button. Use *only* the horizontal and vertical scale adjustments and the trigger menu to complete today's task as you continue to improve your skills.

Use the oscilloscope to adjust the trimpot until $0 < V_2 < V_{DD}$, that is, adjust the trimpot until the BC 337 transistor in operating in the middle of the active region. View both voltages V_1 and V_2 .

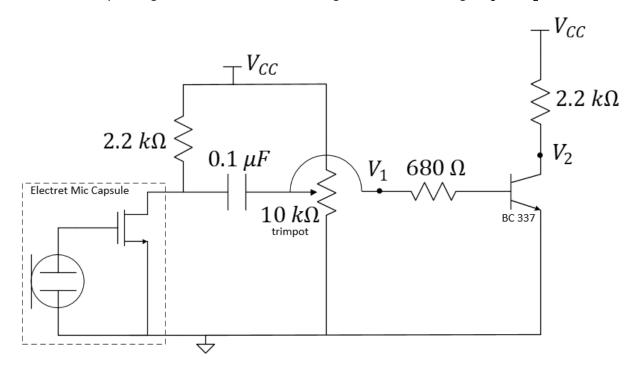


Figure 1: A microphone circuit with extra voltage gain via a BJT.

Connect a loudspeaker to your function generator and produce a low-voltage sinusoid at $2\ kHz$ to verify that V_2 responds to the microphone stimulus. Use the oscilloscope to measure and record the frequency of V_2 . Let your TA know you are ready for evaluation to receive your module credit.

Learning Objectives

- Ability to map a circuit design onto the breadboard in a functional and clean manner.
- Ability to use the oscilloscope.
- Ability to troubleshoot problems that occur during a build.

BC337, BC337-25, BC337-40

Amplifier Transistors

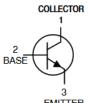
NPN Silicon

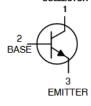
Features

• These are Pb-Free Devices

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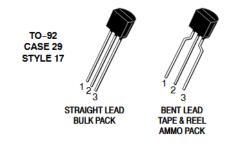


MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	45	Vdc
Collector - Base Voltage	V _{CBO}	50	Vdc
Emitter - Base Voltage	V _{EBO}	5.0	Vdc
Collector Current - Continuous	I _C	800	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	R _{0JA}	200	°C/W
Thermal Resistance, Junction-to-Case	R _{0JC}	83.3	°C/W



CEM-C9745JAD462P2.54R

Revision 0-2010

Omni-Directional Foil Electret Condenser Microphone

DESCRIPTION

PART#

Omni-Directional Foil Electret Microphone, 9.7 mm diameter and 4.5 mm high, Power Supply 5.0 V max, External Resistance Loading of 680 Ω, and sensitivity of -44 dB. Terminated with 2 solder points, Lead Free RoHS Compliant

SPECIFICATION	S:				Schematic Drawing
Direction	Omni Directiona	al Foil Elec			
Operating Voltage Range	Vs= 1.0 Vdc ~ 10.0 Vdc				FET impedance converter Term.1 C
Frequency Range	100 ~ 10,0	000 Hz.			Output
Sensitivity	- 46 ± 2.0, (0 dB = 1	IV / Pa)at	1K Hz		ECM _ RL Unit +Vs
Sensitivity Reduction	3.0 V to 2.0	V -3 dB			unit Term.2 +Vs
Operating Temperature	-20°C to	-20°C to + 60°C			Shield case Ground
Loading Resistance (RL)	External, 680 Ω at Vs =	= 1.5 V, Ma	x. 2,20	0Ω	
Typical Frequency	/ Response	Microphon W	e Respon Vindow	ise Toll	Dimensions Units in: mm Tolerance: ±0.3 mm
(m)		Frequency (Hz)	Lower Limit (dB)	Upper Limit (dB)	4.5±0.2 4.5±0.5 2.0
8 0		50	-6	+3	(#) T
e e	<u> </u>	100	-3	+3	22,200
g-10	 	800	-3	+3	
É-20		1000	0	0	Term 2 Group
Ž.,		1200	-3	+3	GND
20 50 100 200 50	0 1000 2000 5000 10000 20000	3000	-3	+8	
20 00 100 200 500 Env	7 100 200 300 1000 2000 nunci (Ur)	5000	-3	+8	
пе	insurà (uri	10000	-8	+8	